

 $\label{lem:leading sapphire products} Industry-leading sapphire products \\ for next-generation product development and R\&D$





NAPHIA[™] Series

Orbray Co., Ltd., has manufactured a variety of sapphire substrates during the era of LED adoption, and the crystal growth / cleaning / polishing technology we've cultivated through this has evolved further to support the next generation of device development. Our new series of substrates, the NAPHIATM series, is primarily suited for research and development of new semiconductor devices, and can preclude problems caused by other substrates.

In addition to the conventional standard grade, we also offer prime grade, which has a higher level of flatness and cleanliness. Furthermore, with precision cleaning and re-polishing, it can be used repeatedly, contributing to a reduction in total cost.

NAPHIA™ **Sapphire wafers**Standard grade / Prime grade

NAPHIA™ Carrier wafers

NAPHIA™
Sapphire setters (firing process tools)

NAPHIA™ Optical flat lenses/covers $\begin{array}{c} \text{NAPHIA}^{\text{\tiny{M}}} \\ \text{Through-hole wafers} \end{array}$

NAPHIA™ Ceramic wafers NAPHIA™ Contract processing



Orbray's high-quality polishing technology

Utilizing our precision processing, we can customize the off-cut angle and ensure high-quality cleaning to support such applications as epitaxial growth and wafer bonding.

We also offer prime grade wafers, which are characterized by high flatness (TTV < $2\mu m$), low metal contamination (K, Ti, Cr, Mn, Fe, Co, Ni, Cu, $Zn \le 2E10/cm^2$), and low particle contamination ([Particle size $\ge 0.3\mu m$] $\le 0.18pcs/cm^2$).

To meet recent demand for uses such as wafer bonding and other semiconductor processes, we offer high-quality polishing technology for various poly-crystal wafers in addition to sapphire, by applying our prime grade technology.

NAPHIA[™] Sapphire wafers

In addition to standard grade substrates for general LED use, we also offer high-quality prime grade wafers. The high-quality cleaning we apply to prime grade wafers results in low contamination from both particles and metal*.

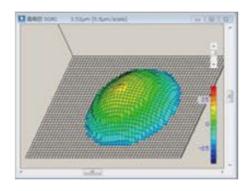
We control flatness (TTV, bow, warp, etc.) with our precision manufacturing technology, to minimize any warpage that can occur during epitaxial growth. Our prime grade wafer is optimal for development of new processes and new products. Applications for prime grade wafers include micro-LED, DUV-LED, RF devices, and GaN / AIN / Ga₂O₃ templates.

^{*} K, Ti, Cr, Mn, Fe, Co, Ni, Cu, Zn < 2E10/cm² with TXRF.

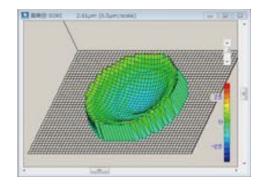
Item	Specificaitons					
Diameter	ф2inch	ф4inch	ф6inch	ф8inch		
Material	Artifical sapphire (Al ₂ O ₃ ≥ 99.99%)					
Thickness	430±15μm	650±15μm	1300±20μm	1300±20μm		
Surface orientation		c-plan	ne (0001)			
OF length	16±1mm	30±1mm	47.5±2.5mm	47.5±2.5mm		
OF orientation	a-plane 0±0.3°					
TTV*	≤10µm	≤10µm	≤15µm	≤15µm		
Bow*	-10μm ~ 0μm	-15μm ~ 0μm	-20μm ~ 0μm	-25μm ~ 0μm		
Warp*	≤15µm	≤20µm	≤25µm	≤30µm		
Remarks		Epi-ready	(Ra<0.3nm)			
Backside finishing	Lapping (Ra 0.6µm - 1.2µm)					
Packaging	Vacuum packaging in cleanroom					
Prime grade	High-quality cleaning: (particle size≥0.3μm) ≤0.18pcs/cm², metal contamination ≤ 2E10/cm²					
Remarks	Customizable specifications: a-/ r-/ m-plane orientation, off-angle, shape, double-side polishing					

^{*}TTV (Total Thickness Variation): The difference between the maximum and minimum values of the wafer thickness.

^{*}Warp: The difference between the maximum and the minimum distances of the median surface of a free, un-clamped wafer from the reference plane defined above.



+Bow (convex): 2.61µm



-Bow (concave): 3.53µm

High-quality products and services for next-generation semiconductor devices and epitaxial growth

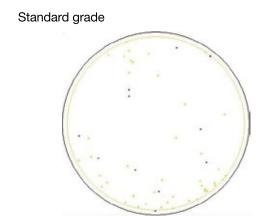
- ·High degree of flatness (controlled TTV, bow, warp etc.)
- ·High-quality cleaning (low particle contamination, low metal contamination)
- ·Substrate drilling, grooving, cutting, and backside polishing
- ·Attachment of data such as cleanliness and shape of substrate (optional)

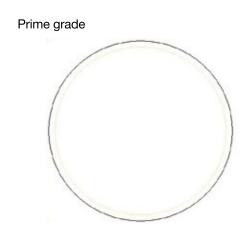
Depending on the specs, we have inventory for substrates of 2 to 8 inches, or up to 300mm in diameter. Please contact us for any inquiries.

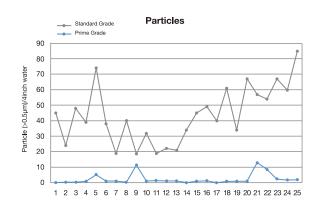
^{*}Bow: The deviation of the center point of the median surface of a free, un-clamped wafer from the reference plane, where the reference plane is defined by the three corners of an equilateral triangle.

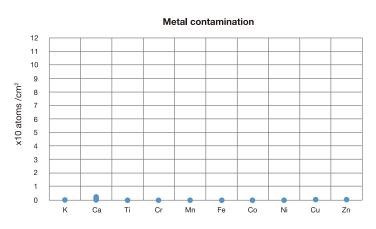
$\square \triangle \square \square \square$ Prime grade wafers

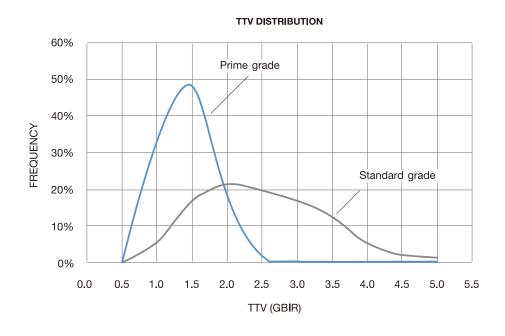
What is prime grade? Our prime grade sapphire wafer has best-in-class quality in terms of flatness and cleanliness. Aiming for the equivalent cleanliness as for silicon wafers, we have produced sapphire wafers with very low metal contamination (≤5E10/cm²). We are currently achieving lower metal contamination than 2E10/cm², which is near the detection limit of our measuring instruments (TXRF).











For single-side polished wafers, the TTV achieved is equivalent to that for double-side polished wafers.

*TTV (GBIR) = Difference in thickness between maximum value and minimum value.

NAPHIA[™] Carrier wafers

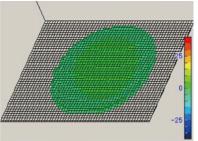
NAPHIA™ sapphire is used in semiconductor processing as a carrier wafer, such as for a support in the handling of ultra-thin device wafers. Utilizing the polishing technology we have cultivated over many years, we are able to manufacture ultra-large support wafers and carrier plates with a diameter of up to 12 inches (300mm). The TTV of carrier wafers is a critical parameter, and our carrier wafer has best-in-class minimal TTV.

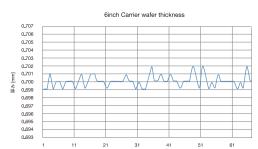
Furthermore, we have the capability of additional processing, such as drilling and grooving, which is available for all specifications. We also offer adapter wafers, which allow the use of small wafers in equipment designed for large wafers.

Compared to glass/ceramics, sapphire has excellent heat, chemical, and plasma resistance, so it can be used in high-temperature processes or harsh environments without distortion or deformation.

Item	Specifications						
Diameter	ф4 inch	ф5 inch	ф6 inch	ф8 inch	ф12 inch		
Materia l	Artificial sapphire (Al₂O₃ ≥ 99.99%)						
Thickness		1±0.003mm 3±0.005mm					
Orientation		c-plane (0001)					
OF	Flat / Notch / None						
TTV							
Frontside finishing	Polish (Ra<0.3nm)						
Backside finishing							
Remarks		Polish (Ra<0.3nm) Customizable specifications: thickness, orientation, single-side polishing. Other options: drilling, laser marking, delivery by thickness classification, re-polishing					









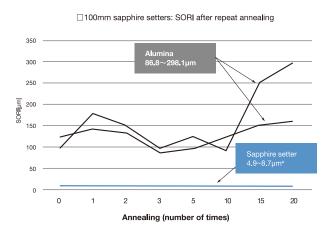


NAPHIA[™] Sapphire setters (firing process tools)

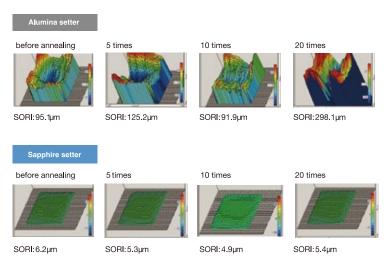
Compared with ceramic setters, our sapphire setters have the advantage of being resistant to deformation even with continuous use, due to the excellent heat resistance of sapphire. We can re-clean or re-process our sapphire setters to allow for reuse, for total cost reduction.

Item	Specifi	cations	
Dimensions	$100 \times 100 \pm 0.5$ mm $150 \times 150 \pm 0.5$ mm		
Thickness	1 ±0.5mm		
SORI	≤20µm ≤40µm		
Surface finishing	Both sides have matte finish Ra≤1µm		

For custom specs, please contact us.



Experiment: Deformation of sapphire setters after repeated annealing
Example: 100mm×1mm thickness sapphire setters (both surfaces have matte finish)
Annealing conditions: 1500°C, nitrogen in atmosphere, 8hours







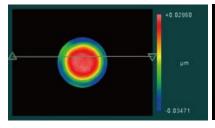
NAPHIA[™] Optical flat lenses / covers

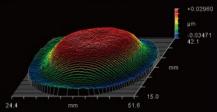
NAPHIATM optical flat lenses / covers are optical windows and lenses that are ultra-precision processed in shape and flatness (indicated by λ) for small diameters such as Φ 1mm to Φ 3mm, and large diameters such as Φ 300mm.

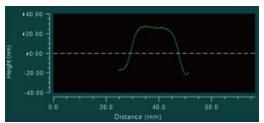
Both circular and square shapes are available. If the thickness is 3mm or more, we can provide a higher degree of flatness. Transparent materials with a minimal difference in thickness have such advantages as the ability to bond to different materials while maintaining flatness, and more uniform transmission of light. Sapphire, as a transparent material, allows for clear visibility of the bonded surface, and offers high temperature resistance, excellent thermal conductivity, scratch resistance, and high durability.

Item	Specifications						
Diameter	ϕ 1mm \sim	ф50mm	ф75mm	ф100mm	ф125mm	ф175mm	ф200mm
Material	Artificial sapphire (Al₂O₃ ≥ 99.99%)						
Thickness	0.5mm \sim	1mm, 5mm, 10mm					
Orientation	c-plane (0001)						
Fronside finishing	Polish (Ra<0.3nm)						
Backside finishing	Polish (Ra<0.3nm)						
Remarks	Cus	Customizable specifications: diameter, thickness, orientation, etc. Other options: re-polishing					

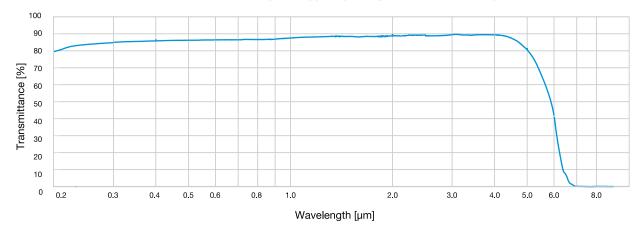
Item	Specifications						
Diameter	□1mm ~	□25mm	□50mm	□75mm	□100mm	□125mm	□150mm
Material	Artificial sapphire (Al ₂ O ₃ ≥ 99.99%)						
Thickness	0.5mm \sim	1mm, 5mm, 10mm					
Orientation	c-plane (0001)						
Frontside finishing	Polish (Ra<0.3nm)						
Backside finishing	Polish (Ra<0.3nm)						
Remarks	Cus	tomizable specific	ations: diameter,	thickness, orientat	ion, etc. Other op	tions: re-polishing	J







Transmittance for c-plane sapphire (0.2~10µm, ultraviolet ~ infrared)



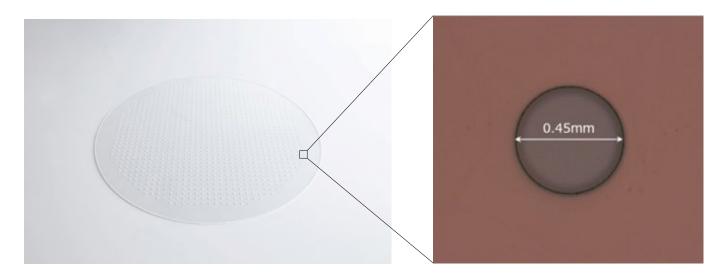
As sapphire provides uniform light transmittance across a wide range of wavelengths, and can be used in harsh environments, it is suitable for ultraviolet and infrared transmission windows and sensor covers. (We can customize lenses/covers according to customers' size requirements and other specifications, such as λ to λ /20.) Sapphire is also used for high-end watch crystals. Moreover, in recent years, it has been increasingly adopted for

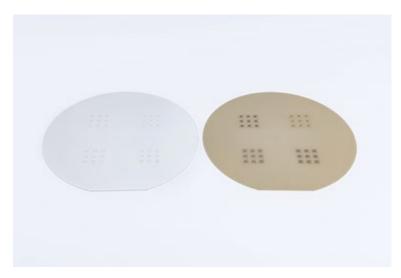
exterior parts for smartphones and smartwatches, with new product designs often incorporating sapphire.

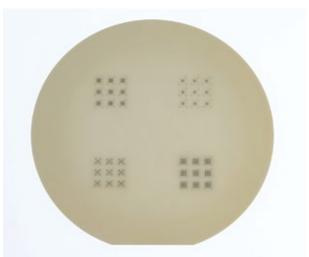
Through-hole wafers (sapphire, AIN, SiC, etc.)

We have drill and laser processing capability. Our NAPHIA™ through-hole sapphire wafers have high surface quality equivalent to that of bare sapphire wafers, and are suitable for semiconductor processing.

We can make through-hole wafers not only from sapphire, but also from other materials (ceramics, silica glass, etc.).







	Example 1	Example 2	Typical value
Hole diameter [µm]	φ100μm	φ700μm	φ50μm~1000μm
Material diameter [mm]	φ150μm	ф80µm	~ф200µm
Material thickness [mm]	0.5mm	1mm	0.25~1mm
TTV [µm]	≤10µm	≤2µm	≤10µm
Number of holes	150 holes / wafer	600 holes/ wafer	-

NAPHIA™ Ceramic wafers (AIN • SiC)

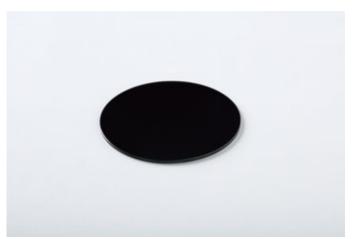
Our NAPHIA™ ceramic wafers are appropriate for semiconductor processes, thanks to the processing technology we have developed through our extensive experience with sapphire wafer polishing. We are able to process any material with minimal damage or grain boundary fractures on the wafer surface, and to a high degree of flatness.

Furthermore, we can do hole processing and cutting of ceramic wafers.

Aluminum Nitride



Sillicon Carbide

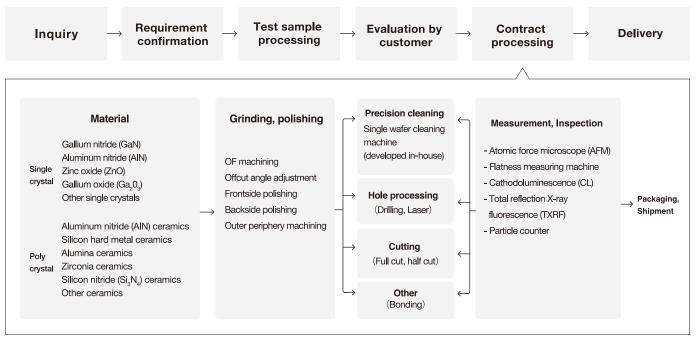


Materia		SiC (Poly crystal)		
Polishing	9	СМР	Mechanical polishing	
Surface Roughness	Ra AFM	0.45nm	0.12nm	
Surface Houghness	P-V AFM	5 . 75nm	0 . 97nm	
Shape	P-V (SORI) * F.T	1.73µm	1 . 65µm	

*Flatness Tester

NAPHIA[™] Contract processing

Utilizing our polishing technology for high-hardness sapphire material, we do contract polishing and grinding of various materials, such as aluminum nitride ceramics, alumina ceramics, and zirconia ceramics. In addition, we can polish single crystals such as gallium nitride (GaN), aluminum nitride (AlN), zinc oxide (ZnO), gallium oxide (Ga_2O_3), and yttrium aluminum garnet (YAG). Please feel free to contact us with any request, as we can also process materials other than those listed. We also offer fine hole processing (drill/laser processing), bonding (atomic bonding), backside polishing, and full cutting (groove processing). For single-crystal materials, we support wafer processing, such as orientation flat processing and off-angle adjustment.



We have a variety of other processes available; please contact us.

Contract processing

Dunnanian	Dun annium annium ant	Work	D		
Processing	Processing equipment	Maximum size	Maximum thickness	Processing accuracy	
	Peripherial blade cutting machine	□200mm	5mm	±0.5mm	
0.485	Inner peripheral blade cutting machine	φ8 inchL150mm	10mm	±0.1mm	
Cutting	Wire cutting machine	φ8 inchL300mm	3mm	±0 . 03mm	
	Dicing machine	□150mm	1.5mm	±0 . 02mm	
	Surface grinder	600×300mm	200mm	0.03mm	
	Horizontal grinder	ф5 inch	50mm		
Surface griding	Vertical grinder	ф8 inch	100mm	±0 . 01mm	
	Double-side lapping machine	φ12 inch	30mm		
	Cylindrical grinder	ф8 inch	300mm	±0.01mm	
Outer periphery grinding	Centerless grinder	L150mm	20mm	0.01mm	
	NC machine	ф300mm	Depends on the proc	essing (please contact us)	
Confess maliables	Double-side lapping machine (Diamond/CMP)	φ12 inch	30mm	.0.005	
Surface polishing	One side polishing machine	φ6 inch	50mm	±0 . 005mm	
B : 111:	Micro drilling	φ12 inch	10mm	ф0 . 25mm	
Drilling	Laser processing machine	ф6 inch	See below		

Laser type	Minimum hole diameter	Minimum pitch	Accuracy	Maximum processing thickness
Femtosecond laser	ф0 . 05mm	0 . 08mm	0.25mm	±0.01mm
UV laser	ф0 . 23mm	0 . 5mm	0 . 8mm	±0.015mm





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